

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1 - 15. (Canceled)

16. (Currently Amended) A solid state imaging element, comprising:

a plurality of pixels arranged in a matrix, each of which has a photoelectric conversion element, a transfer switch for transferring charge stored in said photoelectric conversion element, a charge store part for storing charge transferred by said transfer switch, a reset switch for resetting said charge store part, and

an amplifying element for outputting a signal in accordance with a potential of said charge stored in said charge store part;

wherein a threshold voltage of said amplifying element is reduced in relation to remaining transistors of each pixel, and further wherein a diffusion region that is connected to a power source is laid out to be physically adjacent to the photoelectric conversion element in order to provide an overflow path.

17. (Previously Presented) A solid-state imaging element according to claim 16, wherein said transfer switch is an enhancement type transistor.

18. (Previously Presented) A solid state imaging element according to claim 16, wherein said amplifying element is an enhancement type transistor.

19. (Currently Amended) A solid state imaging element comprising:

a pixel, which has a photoelectric transfer element, a transfer switch for transferring charge stored in said photoelectric transfer element, a charge store part for storing charge transferred by said transfer switch, a reset switch for resetting said charge store part, and an amplifying element for outputting a signal in accordance with a potential of said charge stored in said charge store part;

wherein negative voltage is applied to a gate of said reset switch, and further wherein a threshold voltage of said amplifying element is reduced in relation to remaining transistors of each pixel, and wherein a diffusion region that is connected to a power source is laid out to be physically adjacent to the photoelectric conversion element in order to provide an overflow path.

20. (Previously Presented) The solid state imaging element of claim 16, wherein the amplifying element operates linearly across its entire range of operation.

21. (Previously Presented) The solid state imaging element of claim 17, wherein the amplifying element operates linearly across its entire range of operation.

22. (Previously Presented) The solid state imaging element of claim 18, wherein the amplifying element operates linearly across its entire range of operation.

23. (Previously Presented) The solid state imaging element of claim 19, wherein the amplifying element operates linearly across its entire range of operation.